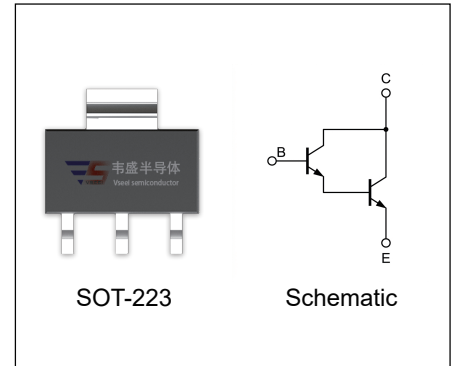


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TRANSISTOR (PNP)

FEATURES

- Complementary to CZT122
- Silicon Power Darlington Transistors
- Low speed switching and amplifier applications



SOT-223

Schematic

MAXIMUM RATINGS (T_a=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V _{CBO}	Collector-Base Voltage	-100	V
V _{CEO}	Collector-Emitter Voltage	-100	V
V _{EBO}	Emitter-Base Voltage	-5	V
I _C	Collector Current -Continuous	-5	A
P _C	Collector Power Dissipation	1	W
R _{θJA}	Thermal Resistance From Junction To Ambient	125	°C/W
T _J , T _{stg}	Operation Junction and Storage Temperature Range	-55~150	°C

ELECTRICAL CHARACTERISTICS (T_a=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	
Collector-base breakdown voltage	V _{(BR)CBO}	I _C =-1m A, I _E =0	-100			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C =-30mA, I _B =0	-100			V
Collector cut-off current	I _{CBO}	V _{CB} =-100V, I _E =0			-200	uA
Base cut-off current	I _{CEO}	V _{CE} =-50V, I _B =0			-500	uA
Emitter cut-off current	I _{EBO}	V _{EB} =-5V, I _C =0			-2	mA
DC current gain	h _{FE(1)}	V _{CE} =-3V, I _C =-0.5A	1000			
	h _{FE(2)}	V _{CE} =-3V, I _C =-3A	1000			
Collector-emitter saturation voltage	V _{CE(sat)1}	I _C =-3A, I _B =-12mA			-2	V
	V _{CE(sat)2}	I _C =-5A, I _B =-20mA			-4	V
Base-emitter voltage	V _{BE(on)}	V _{CE} =-3V, I _C =-3A			-2.5	V
Transition frequency	f _T	V _{CE} =-4V, I _C =-3A, f=1MHz	4			MHz
Collector output capacitance	C _{ob}	V _{CB} =-10V, I _E =0, f=1.0MHz			200	pF